

Semiconductors
High-reliability discrete products and engineering services since 1977

## 1N4448

## SILICON SWITCHING DIODE

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS ( $\mathrm{Sn} / \mathrm{Pb}$ plating), standard, and as RoHS by adding "-PBF" suffix.


## MAXIMUM RATINGS

| Parameter | Symbol | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Repetitive peak reverse voltage | $\mathrm{V}_{\text {RRM }}$ |  | - | 100 | V |
| Continous reverse voltage | $\mathrm{V}_{\mathrm{R}}$ |  | - | 100 | V |
| Continuous forward current ${ }^{(1)}$ | $\mathrm{I}_{\mathrm{F}}$ |  | - | 200 | mA |
| Repeptive peak forward current | $\mathrm{I}_{\text {FRM }}$ |  |  | 450 | mA |
| Non-repetitive peak forward current | $\mathrm{I}_{\text {FSM }}$ | Square wave; $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$ prior to surge $\begin{gathered} t=1 \mu \mathrm{~s} \\ \mathrm{t}=1 \mathrm{~ms} \\ \mathrm{t}=1 \mathrm{~s} \end{gathered}$ | - | $\begin{gathered} 4 \\ 1 \\ 0.5 \end{gathered}$ | A |
| Storage temperature | $\mathrm{T}_{\text {stg }}$ |  | -65 | +200 | ${ }^{\circ} \mathrm{C}$ |
| Junction temperature | $\mathrm{T}_{\mathrm{J}}$ |  | - | 200 | ${ }^{\circ} \mathrm{C}$ |

Note 1: Device mounted on a FR4 printed-circuit board; lead length 10mm
ELECTRICAL CHARACTERISTICS (@TJ $=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Forward voltage | $V_{F}$ |  |  |  | V |
|  |  | $\mathrm{I}_{\mathrm{F}}=5 \mathrm{~mA}$ | 0.62 | 0.72 |  |
|  |  | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ | - | 1 |  |
| Reverse current | $\mathrm{I}_{\mathrm{R}}$ | $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}$ | - | 25 | nA |
| Reverse current | $\mathrm{I}_{\mathrm{R}}$ | $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}, \mathrm{~T}_{\mathrm{J}}=100^{\circ} \mathrm{C}$ | - | 3 | $\mu \mathrm{A}$ |
| Reverse current | $\mathrm{I}_{\mathrm{R}}$ | $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}, 25^{\circ} \mathrm{C} \mathrm{I}_{\mathrm{R}}, \mathrm{T}_{\mathrm{J}}=150^{\circ} \mathrm{C}$ | - | 50 | $\mu \mathrm{A}$ |
| Diode capacitance | $\mathrm{C}_{\mathrm{d}}$ | $\mathrm{f}=1 \mathrm{MHz}, \mathrm{V}_{\mathrm{R}}=0 \mathrm{~V}$ | - | 4 | pF |
| Reverse recovery time | $\mathrm{t}_{\mathrm{rr}}$ | When switched from $I_{F}=10 \mathrm{~mA}$ to $\mathrm{I}_{\mathrm{R}}=$ $60 \mathrm{~mA}, \mathrm{R}_{\mathrm{L}}=100 \Omega$ measured at $\mathrm{I}_{\mathrm{R}}=1 \mathrm{~mA}$ | - | 4 | ns |
| Forward recovery voltage | $\mathrm{V}_{\mathrm{fr}}$ | When switched from $\mathrm{I}_{\mathrm{F}}=50 \mathrm{~mA}, \mathrm{t}_{\mathrm{r}}=20 \mathrm{~ns}$ | - | 2.5 | V |

## THERMAL CHARACTERISTCS

| Parameter | Symbol | Conditions | Value | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Thermal resistance junction to tie-point | $\mathrm{R}_{\mathrm{th}(j-\mathrm{tp})}$ | Lead length 10 mm | 240 |  |
| Thermal resistance from junction to <br> ambient | $\mathrm{R}_{\mathrm{th}(j-\mathrm{a})}$ | Lead length $10 \mathrm{~mm}{ }^{(1)}$ | $\mathrm{K} / \mathrm{W}$ |  |

Note 1: Device mounted on a printed-circuit board without metallization pad.

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MECHANICAL CHARACTERISTICS

| Case: | DO-35 |
| :--- | :--- |
| Marking: | Alpha-numeric |
| Polarity: | Cathode band |



